

ABSTRACT

A semiconductor integrated device comprises: a light-shielding film which shields at least some part of a transfer section of the semiconductor integrated device from 5 light; a first wiring formed in the same layer as the light-shielding film, with one end connected to a pad electrode and an other end extended to a side edge of the semiconductor substrate; a second wiring arranged to go around a side face of the semiconductor substrate, and 10 connected to the first wiring; and a sealing member which seals the solid-state image sensor.